

32 4. (Amended) A semiconductor device according to claim 1, wherein said at least one electrode and said source wiring comprise a same material.

Sub C1 8. (Amended) A semiconductor device according to claim 1, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.

33 9. (Amended) A semiconductor device comprising:
a semiconductor layer formed on an insulating surface, and having at least a source region, a drain region, and a channel formation region interposed therebetween;
a first insulating film formed on said semiconductor layer;
at least one electrode formed on said first insulating film, and overlapping said channel formation region;
a source wiring formed on said first insulating film;
a second insulating film covering at least said at least one electrode and said source wiring;
a gate wiring formed on said second insulating film, and connected to said at least one electrode;
a connection electrode formed on said second insulating film, and connected to said source wiring and said semiconductor layer; and
a pixel electrode formed on said second insulating film, and electrically connected to said semiconductor layer.

34 Sub C1 12. (Amended) A semiconductor device according to claim 9, wherein said at least one electrode comprises a gate electrode.

34 13. (Amended) A semiconductor device according to claim 9, wherein said at least one electrode and said source wiring comprise a same material.

35 sub C1 18. (Amended) A semiconductor device according to claim 9, wherein one pixel including said pixel electrode forms a storage capacitor between said semiconductor layer connected to said pixel electrode and said at least one electrode connected to a gate wiring of an adjacent pixel, using said first insulating film as a dielectric.

Sub C1 20. (Amended) A semiconductor device according to claim 9, said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.

B6 21. (Amended) A semiconductor device comprising:
a first insulating film adjacent to a semiconductor layer, said semiconductor layer having at least a source region, a drain region, and a channel formation region interposed therebetween;
at least one electrode including a gate electrode formed on said first insulating film;
a source wiring formed on said first insulating film;
a second insulating film covering at least said at least one electrode and said source wiring;
a gate wiring electrically connected to said at least one electrode; and
a pixel electrode electrically connected to said semiconductor layer, wherein said gate wiring and said pixel electrode are formed on said second insulating film.

B7 Sub C1 23. (Amended) A semiconductor device according to claim 21, wherein said at least one electrode and said source wiring comprise a same material.

Sub C1 27. (Amended) A semiconductor device according to claim 21, wherein said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.

38 28. (Amended) A semiconductor device comprising a pair of substrates and a liquid crystal interposed therebetween, one of said pair of substrates having at least a pixel portion and a driver circuit, said pixel portion comprising:

a semiconductor layer formed on an insulating surface, and having at least a source region, a drain region and a channel formation region interposed therebetween;

a first insulating film formed on said semiconductor layer;

at least one electrode formed on said first insulating film, and overlapping at least said channel formation region;

a source wiring formed on said first insulating film;

a second insulating film covering at least said at least one electrode and said source wiring;

a gate wiring formed on said second insulating film, and connected to said at least one electrode;

a connection electrode formed on said second insulating film, and connected to said source wiring and said semiconductor layer; and

a pixel electrode formed on said second insulating film, and electrically connected to said semiconductor layer, and

38 wherein another one of said pair of substrates comprises a light-shielding film in which a red color filter and a blue color filter are laminated so as to overlap said semiconductor layer.

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32. (Amended) A semiconductor device according to claim 28, said semiconductor device is one selected from the group consisting of a personal computer, a video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance.

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33. (Amended) A semiconductor device comprising a pair of substrates and a liquid crystal interposed therebetween, one of said pair of substrates having at least a pixel portion and a driver circuit, said pixel portion comprising:

a semiconductor layer formed on an insulating surface, and having at least a source region, a drain region and a channel formation region interposed therebetween;

a first insulating film formed on said semiconductor layer;

at least one electrode formed on said first insulating film, and overlapping at least said channel formation region;

a source wiring formed on said first insulating film;

a second insulating film covering at least said at least one electrode and said source wiring;

a gate wiring formed on said second insulating film, and connected to said at least one electrode; and

a pixel electrode formed on said second insulating film, and electrically connected to said semiconductor layer.

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37. (Amended) A semiconductor device according to claim 33, said semiconductor device is one selected from the group consisting of a personal computer, a

Applicant : Shunpei YAMAZAKI et al.
Serial No. : 09/773,543
Filed : February 2, 2001
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Attorney's Docket No.: 12732-012001 / US4638

B10 video camera, a portable information terminal, a digital camera, a digital video disk player, a portable telephone, an electronic book, a projector, a head mounted type display, and an electric game appliance. --
